



# 2SK2542

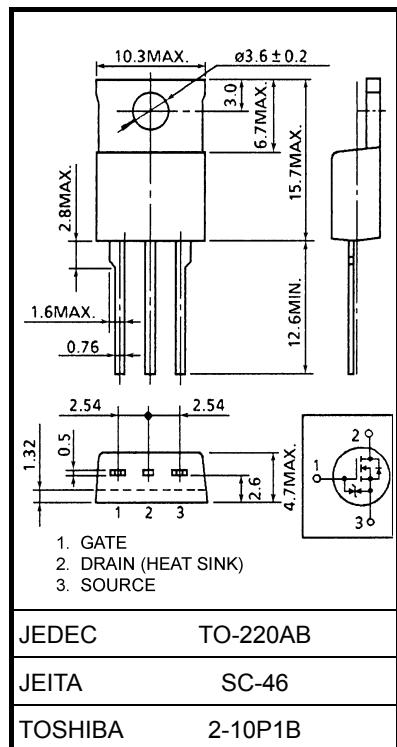
## Switching Regulator Applications

Unit: mm

- 4-V gate drive
- Low drain-source ON-resistance :  $R_{DS\ (ON)} = 0.75\ \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 7.0\ S$  (typ.)
- Low leakage current :  $IDSS = 100\ \mu A$  (max) ( $V_{DS} = 500\ V$ )
- Enhancement mode :  $V_{th} = 2.0$  to  $4.0\ V$  ( $V_{DS} = 10\ V$ ,  $I_D = 1\ mA$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	500	V
Drain-gate voltage ( $R_{GS} = 20\ k\Omega$ )	$V_{DGR}$	500	V
Gate-source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	A
	Pulse (Note 1)	$I_{DP}$	A
Drain power dissipation ( $T_c = 25^\circ C$ )	$P_D$	80	W
Single pulse avalanche energy (Note 2)	$E_{AS}$	312	mJ
Avalanche current	$I_{AR}$	8	A
Repetitive avalanche energy (Note 3)	$E_{AR}$	8	mJ
Channel temperature	$T_{ch}$	150	$^\circ C$
Storage temperature range	$T_{stg}$	-55 to 150	$^\circ C$



Weight: 2.0 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th\ (ch-c)}$	1.56	$^\circ C / W$
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	83.3	$^\circ C / W$

Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$ .

Note 2:  $V_{DD} = 90\ V$ ,  $T_{ch} = 25^\circ C$  (initial),  $L = 8.3\ mH$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = 8\ A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.

**Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Gate-source breakdown voltage	$V_{(\text{BR})\text{GSS}}$	$I_G = \pm 10\text{ }\mu\text{A}, V_{DS} = 0\text{ V}$	$\pm 30$	—	—	$\text{V}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	500	—	—	$\text{V}$
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	$\text{V}$
Drain-source ON-resistance	$R_{DS}\text{ (ON)}$	$V_{GS} = 10\text{ V}, I_D = 4\text{ A}$	—	0.75	0.85	$\Omega$
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 4\text{ A}$	3.5	7.0	—	$\text{S}$
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1300	—	$\text{pF}$
Reverse transfer capacitance	$C_{rss}$		—	130	—	
Output capacitance	$C_{oss}$		—	400	—	
Switching time	Rise time	$t_r$	 $V_{GS}$ 10 V $V_{GS}$ 0 V $I_D = 4\text{ A}$ $R_L = 50\Omega$ $V_{DD} \approx 200\text{ V}$ Duty $\leq 1\%$ , $t_w = 10\text{ }\mu\text{s}$	—	26	—
	Turn-on time	$t_{on}$		—	45	—
	Fall time	$t_f$		—	40	—
	Turn-off time	$t_{off}$		—	140	—
Total gate charge (Gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	—	30	—	$\text{nC}$
Gate-source charge	$Q_{gs}$		—	17	—	
Gate-drain ("miller") charge	$Q_{gd}$		—	13	—	

**Source-Drain Ratings and Characteristics ( $T_a = 25^\circ\text{C}$ )**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	8	$\text{A}$
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	32	$\text{A}$
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 8\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	$\text{V}$
Reverse recovery time	$t_{rr}$	$I_{DR} = 8\text{ A}, V_{GS} = 0\text{ V}$ $dI_{DR} / dt = 100\text{ A} / \mu\text{s}$	—	1200	—	$\text{ns}$
Reverse recovery charge	$Q_{rr}$		—	10	—	$\mu\text{C}$

**Marking**